

# What Gas Concentrator Does in Focused Ion Beam System?

Applicable to Focused Electron Beam Systems and Broad-Beam Apparatus

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# Outline

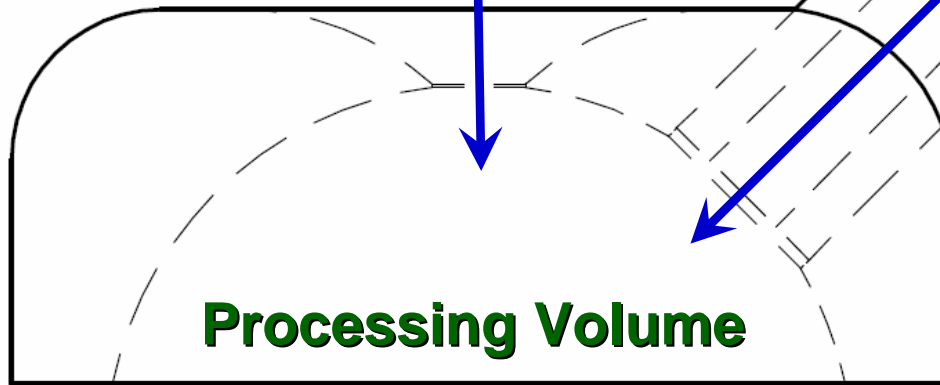
- ◆ **Gas pressure considerations**
- ◆ **Electron optics considerations**
- ◆ **Endpoint detection considerations**
- ◆ **References**

# CUPOLA Gas Concentrator

**Main Chamber Volume with  
Pressure  $\sim 10E-6$  Torr**

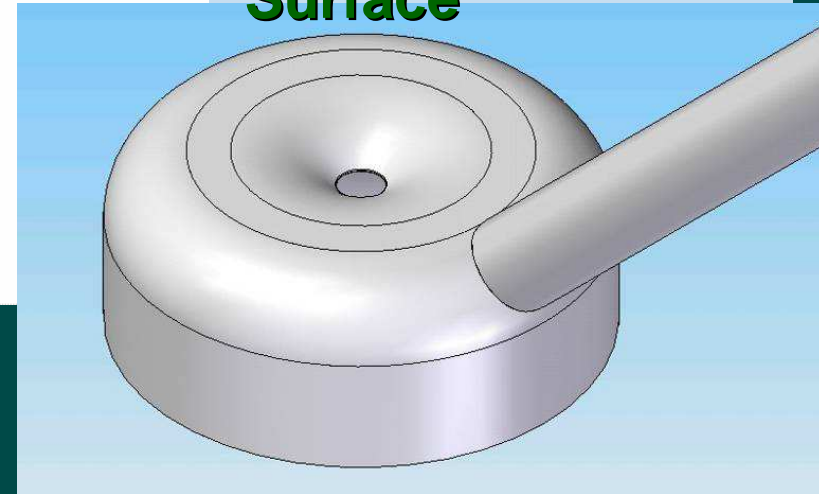
**Beam Pass**

**Gas Injection**



**Processing Volume  
with mTorr Pressure**

**Mirror - Polished  
Surface**

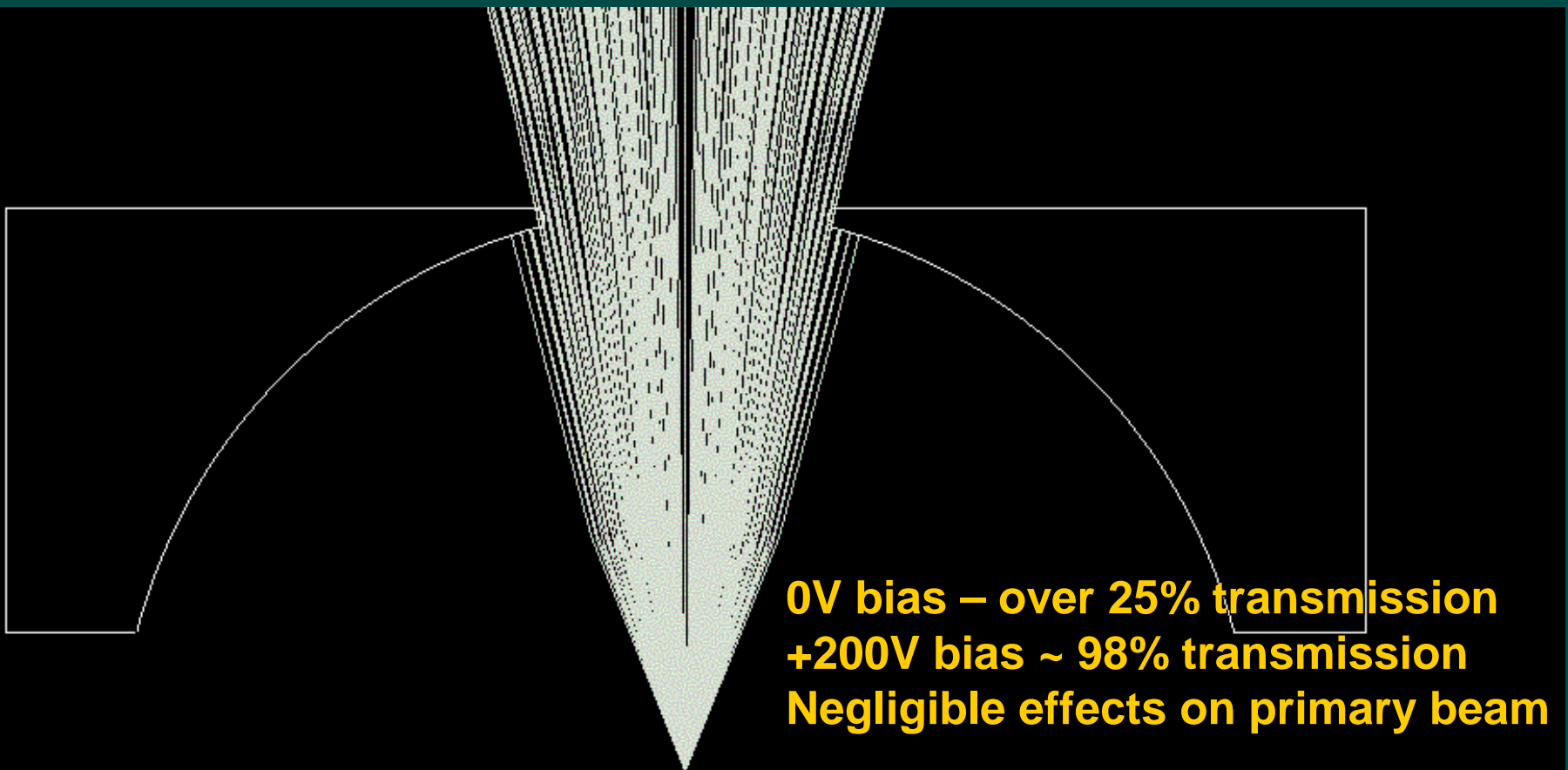


# Gas Pressure Considerations

- ◆ **Pressure in low mTorr range within  $\sim 2 \text{ mm}^3$  process volume, optimal for GAE and deposition**
  - » **Beam path in high pressure ambient minimized and scattering of the primary beam is reduced**
- ◆ **System chamber maintained at  $\sim 10\text{E-}6$  Torr**
  - » **Reduced damage to main chamber components by the reactive process gases**

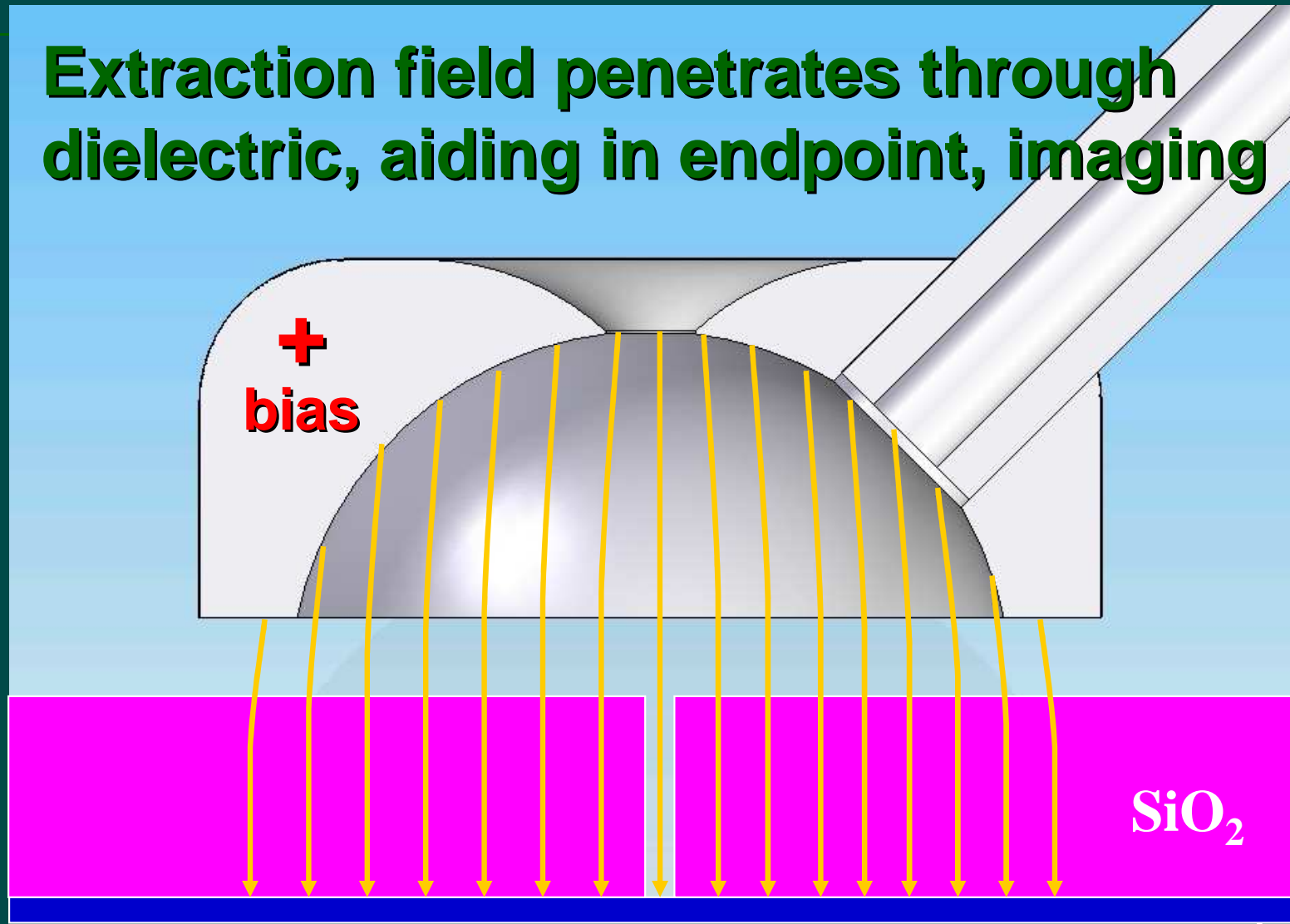
# Electron Optics Considerations

**Concentrator effectively transmits secondary electrons**

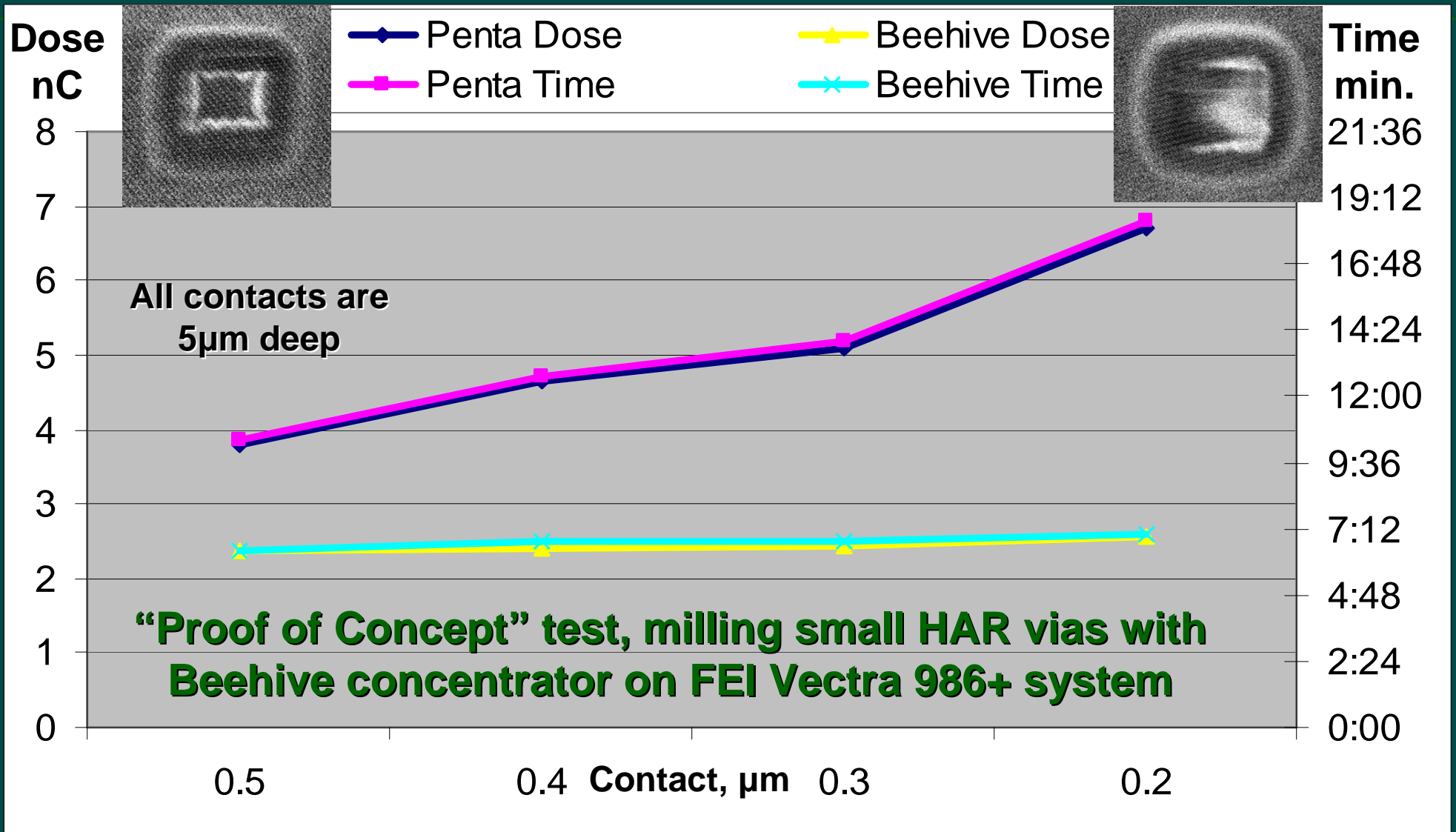


# Endpoint Detection Considerations

Extraction field penetrates through dielectric, aiding in endpoint, imaging



# Throughput Considerations



# Summary

- ◆ **Positively-biased gas concentrator in particle beam processing tool improves**
  - » **Gas pressure regime**
  - » **Imaging concurrent with processing**
  - » **Endpoint detection**
  - » **Enhances milling throughput**



# References

- ◆ V. Ray “Virtual process chamber.....” EIPBN 2004 and JVST B 2004
- ◆ V. Ray “High-throughput HAR via milling” EFUG and ISTFA 2005
- ◆ C. Rue et. al. “Backside circuit edit on full thickness Si devices” ISTFA 2008